



**America Semiconductor**

**Silicon Standard  
Recovery Diode**

**1N2133A thru  
1N2138AR**

**$V_{RRM} = 50\text{ V} - 600\text{ V}$**

**$I_F = 60\text{ A}$**

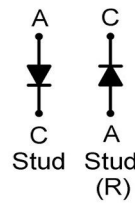
**Features**

- High Surge Capability
- Types up to 600 V  $V_{RRM}$

**Note:**

1. Standard polarity: Stud is cathode.
2. Reverse polarity (R): Stud is anode.
3. Stud is base.

**DO-5 Package**



**Maximum ratings, at  $T_j = 25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	1N2133A(R)	1N2135A(R)	1N2137A(R)	1N2138A(R)	Unit
Repetitive peak reverse voltage	$V_{RRM}$		300	400	500	600	V
RMS reverse voltage	$V_{RMS}$		210	280	350	420	V
DC blocking voltage	$V_{DC}$		50	100	150	200	V
Continuous forward current	$I_F$	$T_C \leq 150\text{ °C}$	60	60	60	60	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}, t_p = 8.3\text{ ms}$	1050	1050	1050	1050	A
Operating temperature	$T_j$		-65 to 200	-65 to 200	-65 to 200	-65 to 200	°C
Storage temperature	$T_{stg}$		-65 to 200	-65 to 200	-65 to 200	-65 to 200	°C

**Electrical characteristics, at  $T_j = 25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	1N2133A(R)	1N2135A(R)	1N2137A(R)	1N2138A(R)	Unit
Diode forward voltage	$V_F$	$I_F = 60\text{ A}, T_j = 25\text{ °C}$	1.1	1.1	1.1	1.1	V
Reverse current	$I_R$	$V_R = 50\text{ V}, T_j = 25\text{ °C}$	10	10	10	10	$\mu\text{A}$
		$V_R = 50\text{ V}, T_j = 150\text{ °C}$	15	15	15	15	mA

**Thermal characteristics**

Thermal resistance, junction - case	$R_{thJC}$		0.65	0.65	0.65	0.65	°C/W
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